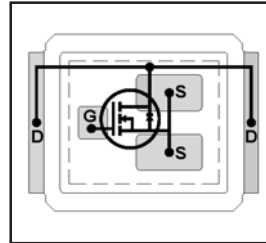


IRF6608/IRF6608TR1

HEXFET® Power MOSFET

- Application Specific MOSFETs
- Ideal for CPU Core DC-DC Converters
- Low Conduction Losses
- Low Switching Losses
- Low Profile (<0.7 mm)
- Dual Sided Cooling Compatible
- Compatible with existing Surface Mount Techniques

V_{DS}	$R_{DS(on)}$ max	Q_g
30V	$9.0m\Omega @ V_{GS} = 10V$	16nC
	$11m\Omega @ V_{GS} = 4.5V$	



Description

The IRF6608 combines the latest HEXFET® Power MOSFET Silicon technology with the advanced DirectFET™ packaging to achieve the lowest on-state resistance in a package that has the footprint of a MICRO-8 and only 0.7 mm profile. The DirectFET package is compatible with existing layout geometries used in power applications, PCB assembly equipment and vapor phase, infra-red or convection soldering techniques, when application note AN-1035 is followed regarding the manufacturing methods and processes. The DirectFET package allows dual sided cooling to maximize thermal transfer in power systems, IMPROVING previous best thermal resistance by 80%.

The IRF6608 balances both low resistance and low charge along with ultra low package inductance to reduce both conduction and switching losses. The reduced total losses make this product ideal for high efficiency DC-DC converters that power the latest generation of processors operating at higher frequencies. The IRF6608 has been optimized for parameters that are critical in synchronous buck converters including $R_{DS(on)}$, gate charge and C_{dv}/dt -induced turn on immunity. The IRF6608 has been optimized for parameters that are critical in synchronous buck converters including $R_{DS(on)}$ and gate charge to minimize losses in the control FET socket.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 12	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	55	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	13	
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	10	
I_{DM}	Pulsed Drain Current ①	100	
$P_D @ T_A = 25^\circ C$	Power Dissipation ⑤	2.1	W
$P_D @ T_A = 70^\circ C$	Power Dissipation ⑤	1.4	
$P_D @ T_C = 25^\circ C$	Power Dissipation	42	
	Linear Derating Factor	0.017	W/°C
T_J	Operating Junction and	-40 to + 150	°C
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ④	—	58	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⑤	12.5	—	
$R_{\theta JA}$	Junction-to-Ambient ⑥	20	—	
$R_{\theta JC}$	Junction-to-Case ⑦	—	3.0	
$R_{\theta J-PCB}$	Junction-to-PCB Mounted	1.0	—	

Notes ① through ⑦ are on page 10

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IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

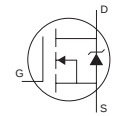
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	29	—	mV/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	7.0	9.0	$m\Omega$	$V_{GS} = 10V, I_D = 13A$ ③
		—	8.0	11		$V_{GS} = 4.5V, I_D = 10A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-5.4	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	30	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -12V$
g_{fs}	Forward Transconductance	28	—	—	S	$V_{DS} = 15V, I_D = 8.8A$
Q_g	Total Gate Charge	—	16	24	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 8.8A$ See Fig. 16
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	4.6	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	1.4	—		
Q_{gd}	Gate-to-Drain Charge	—	5.3	—		
Q_{godr}	Gate Charge Overdrive	—	4.7	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	6.7	—		
Q_{oss}	Output Charge	—	11	—	nC	$V_{DS} = 15V, V_{GS} = 0V$
$t_{d(on)}$	Turn-On Delay Time	—	13	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ ③ $I_D = 8.8A$ Clamped Inductive Load
t_r	Rise Time	—	12	—		
$t_{d(off)}$	Turn-Off Delay Time	—	16	—		
t_f	Fall Time	—	3.4	—		
C_{iss}	Input Capacitance	—	2120	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	440	—		$V_{DS} = 15V$
C_{rss}	Reverse Transfer Capacitance	—	260	—		$f = 1.0MHz$

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	54	mJ
I_{AR}	Avalanche Current ①	—	8.8	A
E_{AR}	Repetitive Avalanche Energy ①	—	0.21	mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	13	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	100		
V_{SD}	Diode Forward Voltage	—	0.94	1.2	V	$T_J = 25^\circ\text{C}, I_S = 8.8A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	31	47	ns	$T_J = 25^\circ\text{C}, I_F = 8.8A$
Q_{rr}	Reverse Recovery Charge	—	33	50	nC	$di/dt = 100A/\mu s$ ③



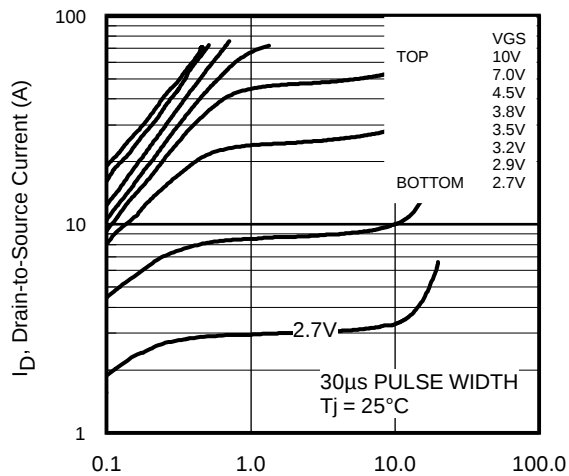


Fig 1. Typical Output Characteristics

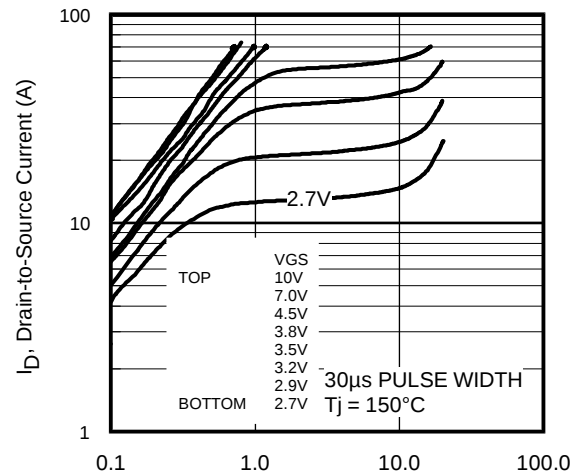


Fig 2. Typical Output Characteristics

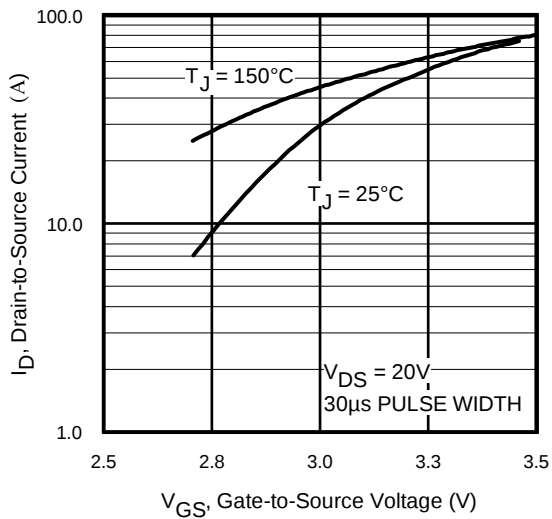


Fig 3. Typical Transfer Characteristics

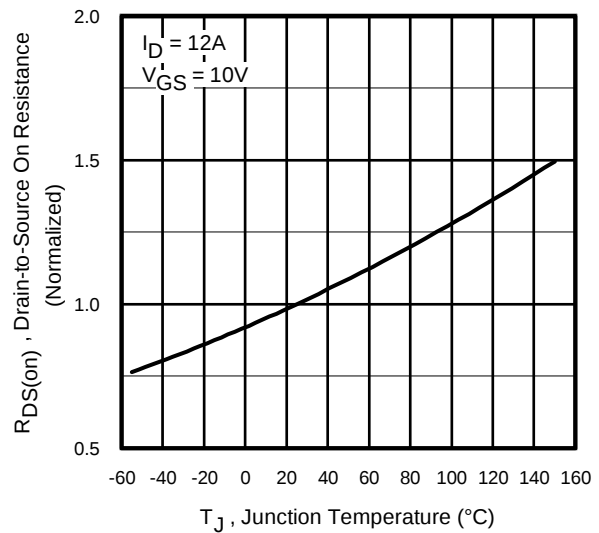
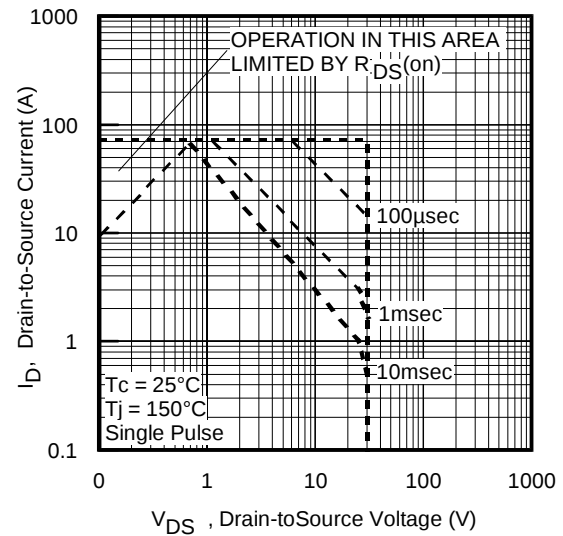
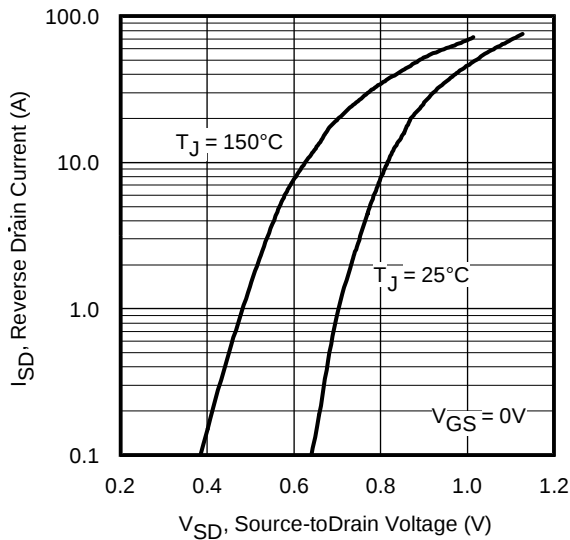
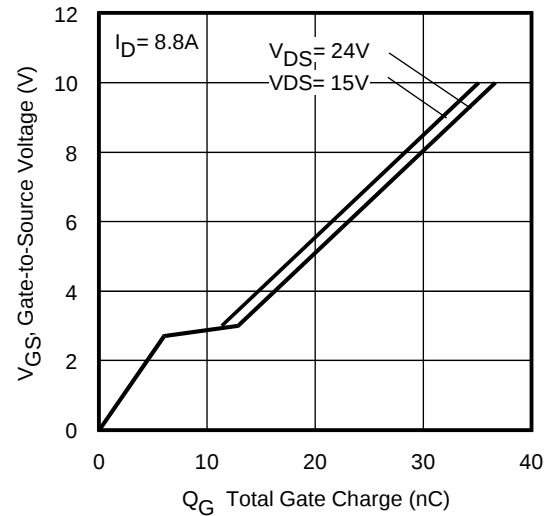
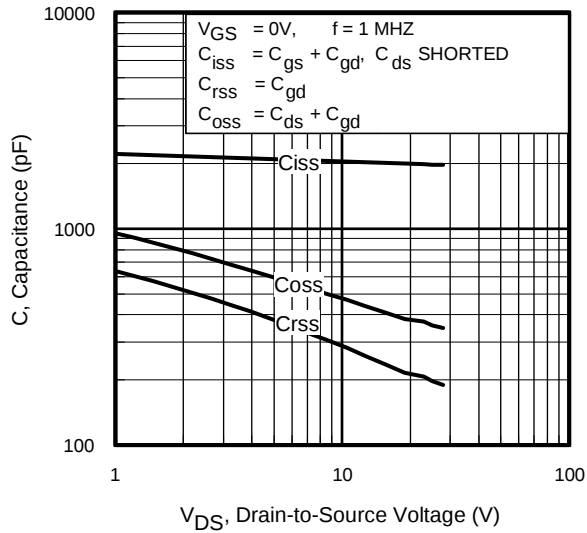


Fig 4. Normalized On-Resistance Vs. Temperature

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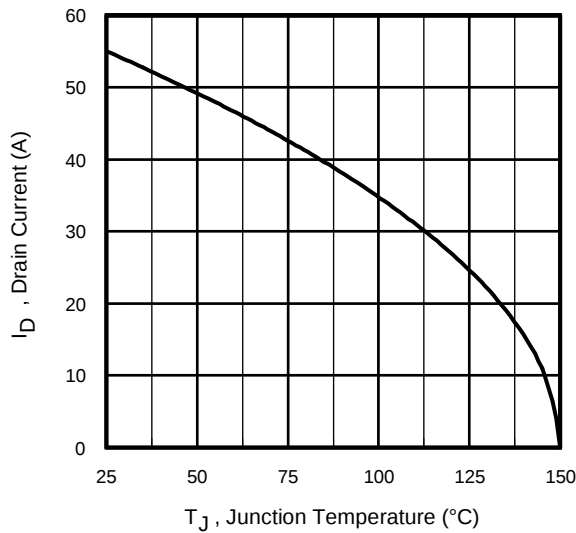


Fig 9. Maximum Drain Current Vs. Case Temperature

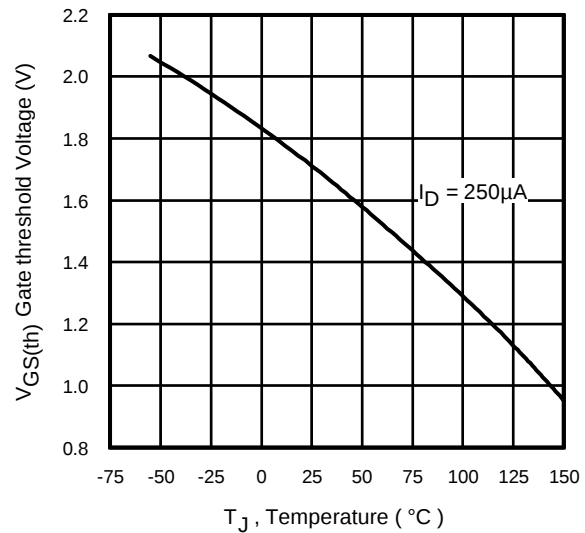


Fig 10. Threshold Voltage Vs. Temperature

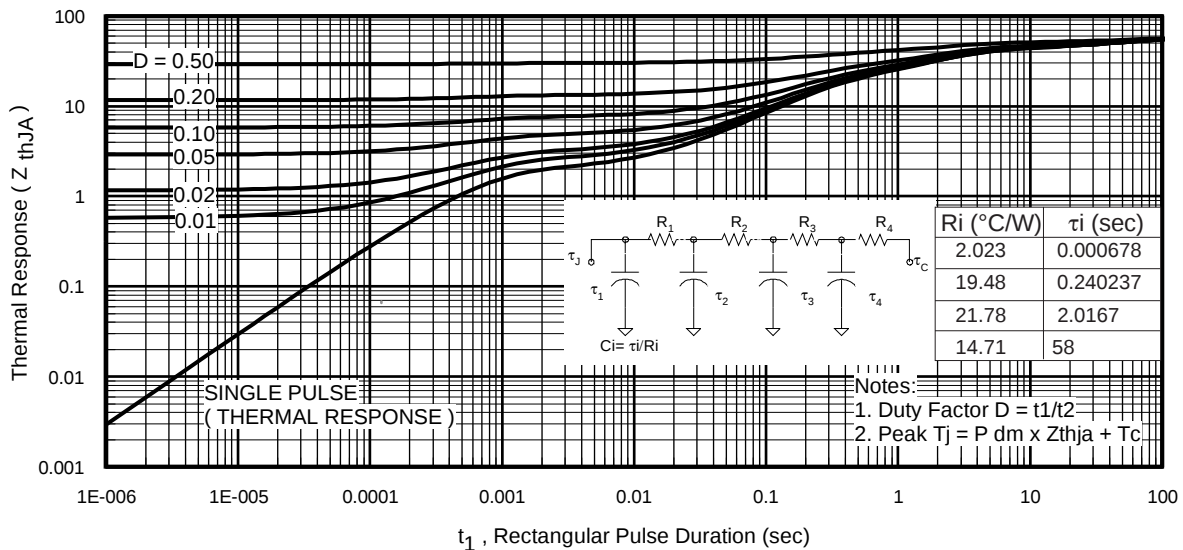


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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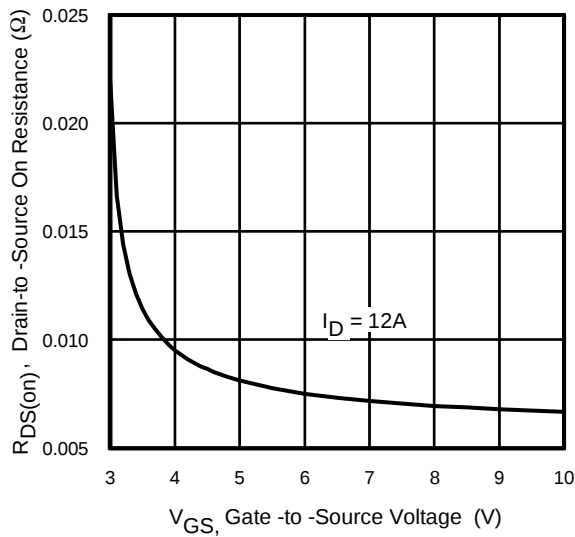


Fig 12. Typical On-Resistance Vs. Gate Voltage

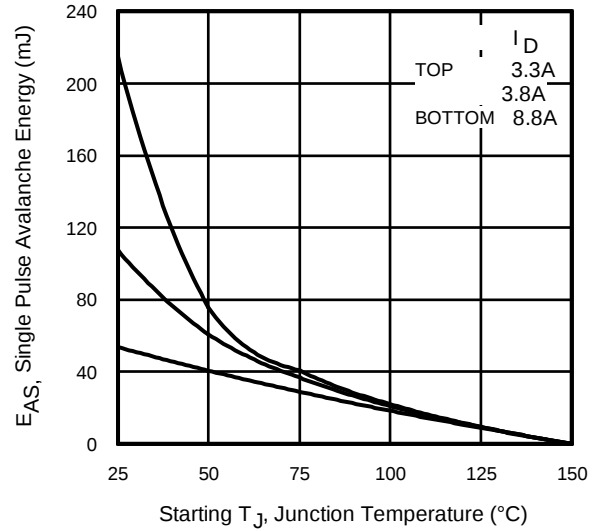


Fig 13c. Maximum Avalanche Energy Vs. Drain Current

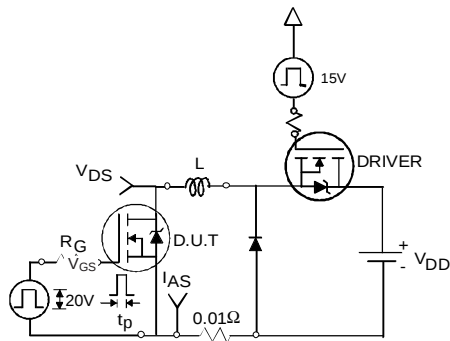


Fig 14a. Unclamped Inductive Test Circuit

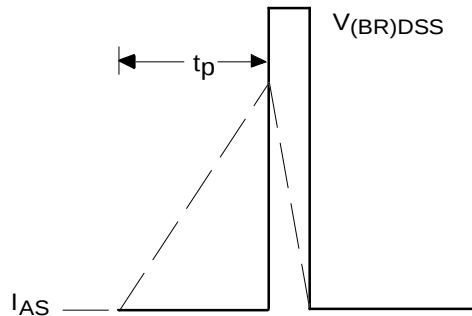


Fig 14b. Unclamped Inductive Waveforms

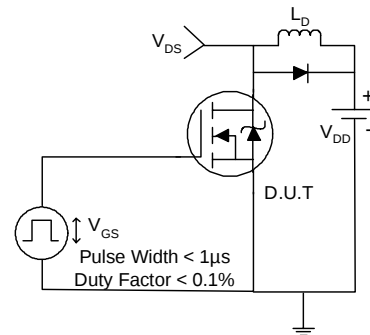


Fig 15a. Switching Time Test Circuit

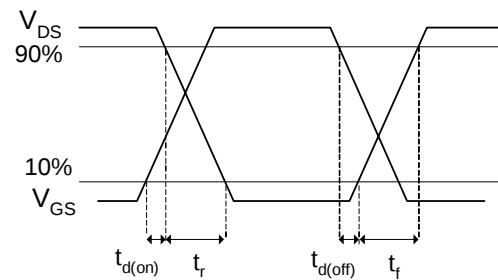


Fig 15b. Switching Time Waveforms

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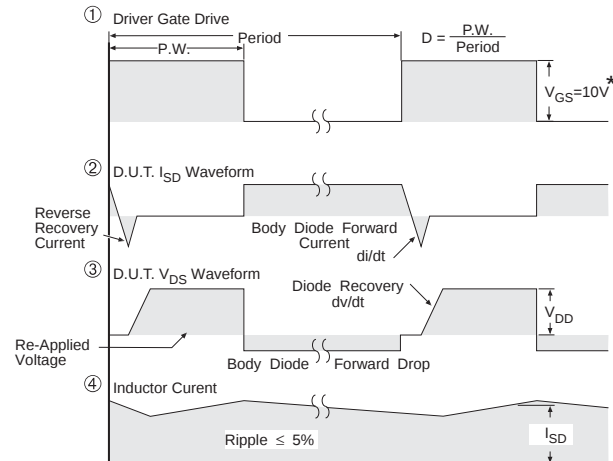
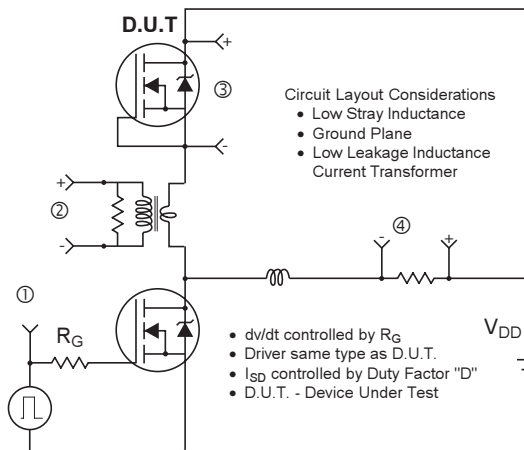


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

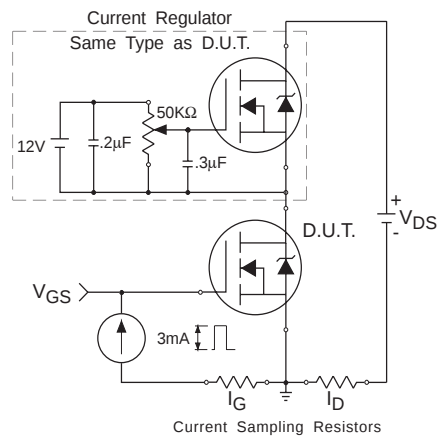


Fig 17. Gate Charge Test Circuit

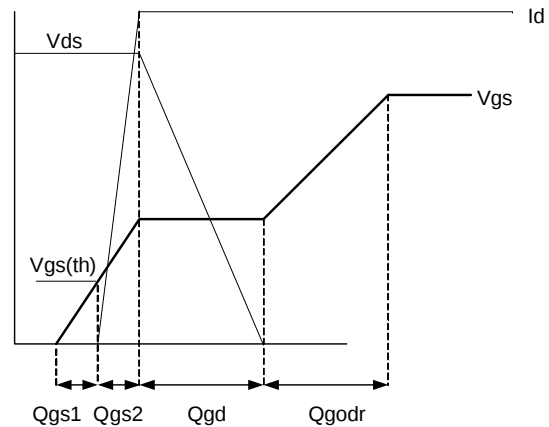


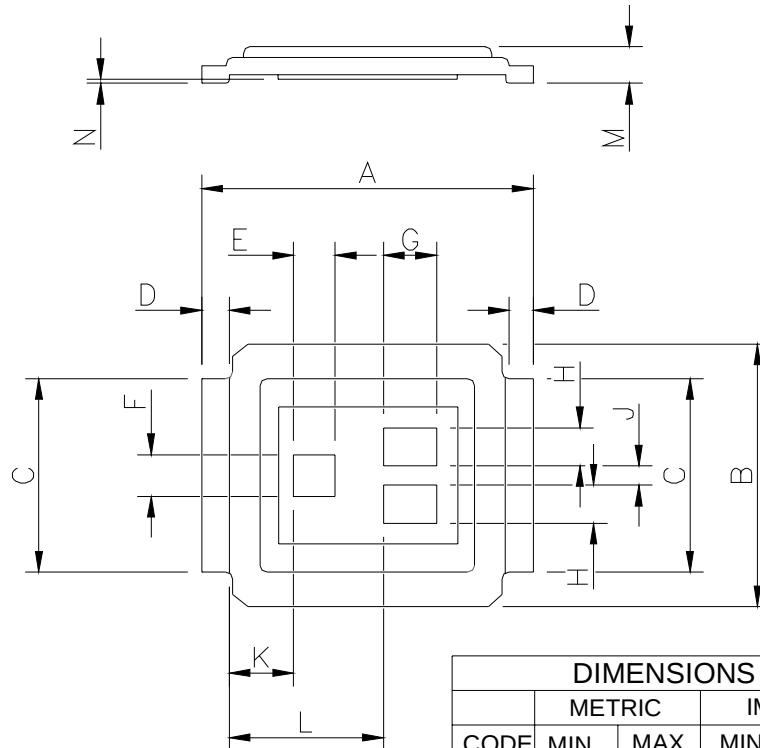
Fig 18. Gate Charge Waveform

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International
IR Rectifier

DirectFET™ Outline Dimension, ST Outline (Small Size Can, T-Designation).

Please see DirectFET application note AN-1035 for all details regarding the assembly of DirectFET. This includes all recommendations for stencil and substrate designs.

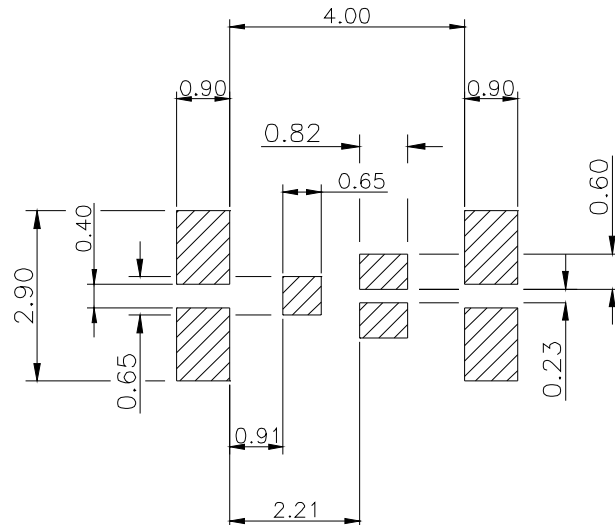


Note: Controlling
dimensions are in mm

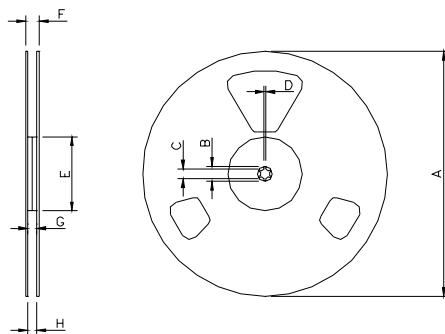
DIMENSIONS				
	METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX
A	4.75	4.85	0.187	0.191
B	3.70	3.95	0.146	0.156
C	2.75	2.85	0.108	0.112
D	0.35	0.45	0.014	0.018
E	0.58	0.62	0.023	0.024
F	0.58	0.62	0.023	0.024
G	0.75	0.79	0.030	0.031
H	0.53	0.57	0.021	0.022
J	0.26	0.30	0.010	0.012
K	0.88	0.98	0.035	0.039
L	2.18	2.28	0.086	0.090
M	0.48	0.58	0.019	0.023
N	0.03	0.08	0.001	0.003

DirectFET™ Board Footprint, ST Outline (Small Size Can, T-Designation).

Please see DirectFET application note AN-1035 for all details regarding the assembly of DirectFET. This includes all recommendations for stencil and substrate designs.

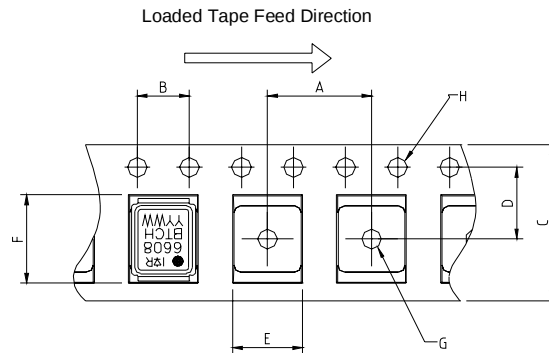


DirectFET™ Tape & Reel Dimension (Showing component orientation).



NOTE: Controlling dimensions in mm
Std reel quantity is 4800 parts. (ordered as IRF6618). For 1000 parts on 7" reel,
order IRF6618TR1

REEL DIMENSIONS									
STANDARD OPTION (QTY 4800)					TR1 OPTION (QTY 1000)				
	METRIC		IMPERIAL			METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
A	330.0	N.C	12.992	N.C	177.77	N.C	6.9	N.C	
B	20.2	N.C	0.795	N.C	19.06	N.C	0.75	N.C	
C	12.8	13.2	0.504	0.520	13.5	12.8	0.53	0.50	
D	1.5	N.C	0.059	N.C	1.5	N.C	0.059	N.C	
E	100.0	N.C	3.937	N.C	58.72	N.C	2.31	N.C	
F	N.C	18.4	N.C	0.724	N.C	13.50	N.C	0.53	
G	12.4	14.4	0.488	0.567	11.9	12.01	0.47	N.C	
H	11.9	15.4	0.469	0.606	11.9	12.01	0.47	N.C	



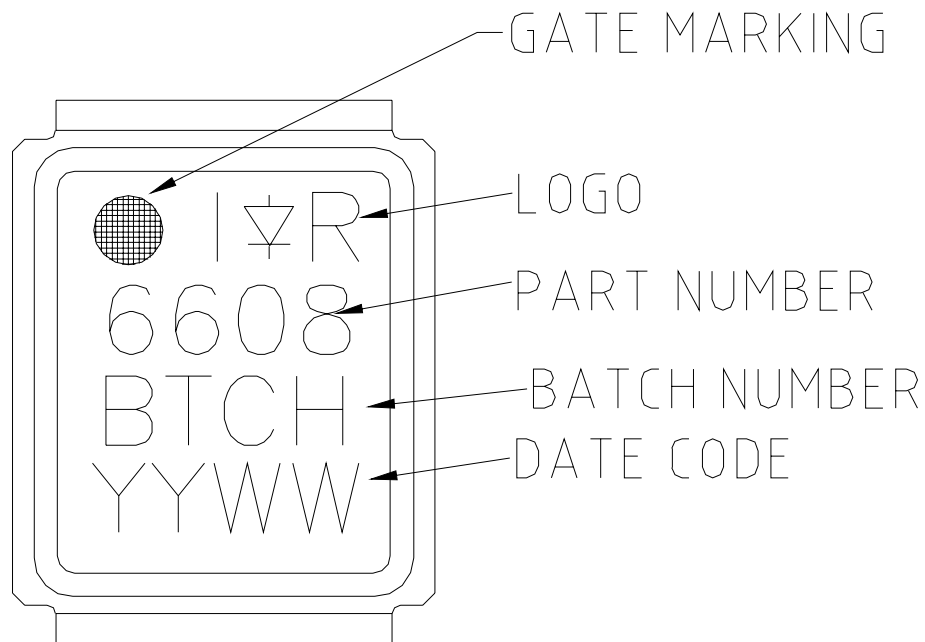
NOTE: CONTROLLING
DIMENSIONS IN MM

DIMENSIONS				
CODE	METRIC		IMPERIAL	
	MIN	MAX	MIN	MAX
A	7.90	8.10	0.311	0.319
B	3.90	4.10	0.154	0.161
C	11.90	12.30	0.469	0.484
D	5.45	5.55	0.215	0.219
E	5.10	5.30	0.201	0.209
F	6.50	6.70	0.256	0.264
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

IRF6608/IRF6608TR1

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DirectFET™ Part Marking



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.38\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 8.8\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ Surface mounted on 1 in. square Cu board.
- ⑤ Used double sided cooling, mounting pad.
- ⑥ Mounted on minimum footprint full size board with metalized back and with small clip heatsink.
- ⑦ T_C measured with thermal couple mounted to top (Drain) of part.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.

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IR Rectifier

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TAC Fax: (310) 252-7903

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